74AVC8T245

8-bit dual supply translating transceiver with configurable voltage translation; 3-state

Rev. 6 — 31 March 2020

Product data sheet

1. General description

The 74AVC8T245 is an 8-bit, dual supply transceiver that enables bidirectional level translation. It features two 8-bit input-output ports (An and Bn), a direction control input (DIR), a output enable input (\overline{OE}) and dual supply pins ($V_{CC(A)}$ and $V_{CC(B)}$). Both $V_{CC(A)}$ and $V_{CC(B)}$ can be supplied at any voltage between 0.8 V and 3.6 V making the device suitable for translating between any of the low voltage nodes (0.8 V, 1.2 V, 1.5 V, 1.8 V, 2.5 V and 3.3 V). Pins An, \overline{OE} and DIR are referenced to $V_{CC(A)}$ and pins Bn are referenced to $V_{CC(B)}$. A HIGH on DIR allows transmission from An to Bn and a LOW on DIR allows transmission from Bn to An. The output enable input (\overline{OE}) can be used to disable the outputs so the buses are effectively isolated.

The device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing any damaging backflow current through the device when it is powered down. In suspend mode when either $V_{CC(A)}$ or $V_{CC(B)}$ are at GND level, both An and Bn are in the high-impedance OFF-state.

2. Features and benefits

- Wide supply voltage range:
 - V_{CC(A)}: 0.8 V to 3.6 V
 - V_{CC(B)}: 0.8 V to 3.6 V
- Complies with JEDEC standards:
 - JESD8-12 (0.8 V to 1.3 V)
 - JESD8-11 (0.9 V to 1.65 V)
 - JESD8-7 (1.2 V to 1.95 V)
 - JESD8-5 (1.8 V to 2.7 V)
 - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114E Class 3B exceeds 8000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101C exceeds 1000 V
- Maximum data rates:
 - 380 Mbit/s (≥ 1.8 V to 3.3 V translation)
 - 260 Mbit/s (≥ 1.1 V to 3.3 V translation)
 - 260 Mbit/s (≥ 1.1 V to 2.5 V translation)
 - 210 Mbit/s (≥ 1.1 V to 1.8 V translation)
 - 150 Mbit/s (≥ 1.1 V to 1.5 V translation)
 - 100 Mbit/s (≥ 1.1 V to 1.2 V translation)
- Suspend mode
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



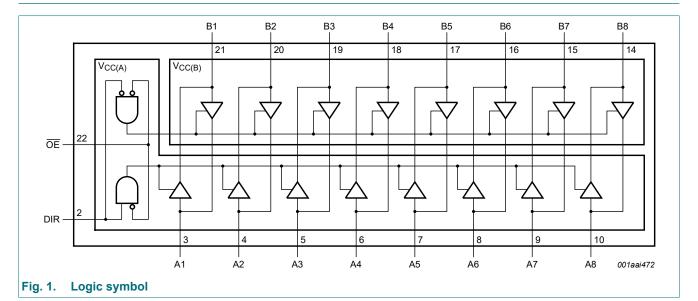
8-bit dual supply translating transceiver with configurable voltage translation; 3-state

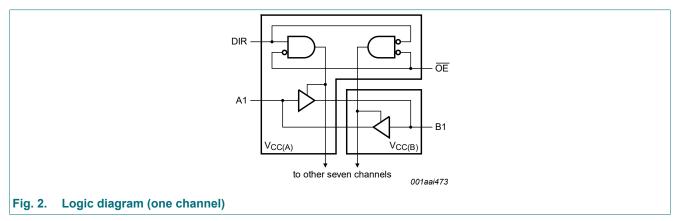
3. Ordering information

Table 1. Ordering information

Type number	Package						
	Temperature range	Name	Description	Version			
74AVC8T245PW	-40 °C to +125 °C	TSSOP24	plastic thin shrink small outline package; 24 leads; body width 4.4 mm	SOT355-1			
74AVC8T245BQ	-40 °C to +125 °C	DHVQFN24	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 24 terminals; body 3.5 x 5.5 x 0.85 mm	SOT815-1			

4. Functional diagram

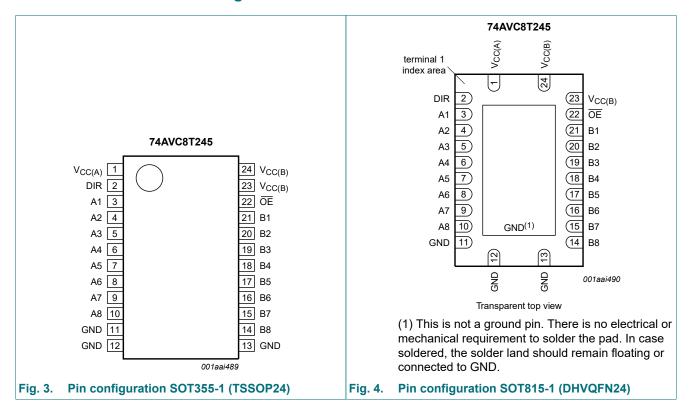




8-bit dual supply translating transceiver with configurable voltage translation; 3-state

5. Pinning information

5.1. Pinning



5.2. Pin description

Table 2. Pin description

Symbol	Pin	Description
V _{CC(A)}	1	supply voltage A (An, $\overline{\text{OE}}$ and DIR inputs are referenced to $V_{\text{CC(A)}}$)
DIR	2	direction control
A1, A2, A3, A4, A5, A6, A7, A8	3, 4, 5, 6, 7, 8, 9, 10	data input or output
GND [1]	11, 12, 13	ground (0 V)
B1, B2, B3, B4, B5, B6, B7, B8	21, 20, 19, 18, 17, 16, 15, 14	data input or output
ŌĒ	22	output enable input (active LOW)
$V_{CC(B)}$	23, 24	supply voltage B (Bn inputs are referenced to $V_{\text{CC(B)}}$)

[1] All GND pins must be connected to ground (0 V).

8-bit dual supply translating transceiver with configurable voltage translation; 3-state

6. Functional description

Table 3. Function table

H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

Supply voltage	Input		Input/output [1]		
$V_{CC(A)}, V_{CC(B)}$	OE [2]	DIR [2]	An [2]	Bn	
0.8 V to 3.6 V	L	L	An = Bn	input	
0.8 V to 3.6 V	L	Н	input	Bn = An	
0.8 V to 3.6 V	Н	X	Z	Z	
GND [1]	X	X	Z	Z	

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC(A)}	supply voltage A		-0.5	+4.6	V
V _{CC(B)}	supply voltage B		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage	[1]	-0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode [1] [2] [3]	-0.5	V _{CCO} + 0.5	V
		Suspend or 3-state mode [1]	-0.5	+4.6	V
Io	output current	$V_O = 0 V \text{ to } V_{CC}$	-	±50	mA
Icc	supply current	per V _{CC(A)} or V _{CC(B)} pin	-	100	mA
I_{GND}	ground current	per GND pin	-100	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C to } +125 ^{\circ}\text{C}$ [4]	-	500	mW

The minimum input voltage ratings and output voltage ratings may be exceeded if the input and output current ratings are observed.

If at least one of $V_{CC(A)}$ or $V_{CC(B)}$ is at GND level, the device goes into suspend mode. The An, DIR and \overline{OE} input circuit is referenced to $V_{CC(A)}$; The Bn input circuit is referenced to $V_{CC(B)}$.

 V_{CCO} is the supply voltage associated with the output port. [2]

 V_{CCO} + 0.5 V should not exceed 4.6 V. [3]

For SOT355-1 (TSSOP24) package: Ptot derates linearly with 12.4 mW/K above 110 °C. For SOT815-1 (DHVQFN24) package: Ptot derates linearly with 15.0 mW/K above 117 °C.

8-bit dual supply translating transceiver with configurable voltage translation; 3-state

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CC(A)}	supply voltage A			8.0	3.6	V
V _{CC(B)}	supply voltage B			8.0	3.6	V
VI	input voltage			0	3.6	V
Vo	output voltage	Active mode	[1]	0	V _{cco}	V
		Suspend or 3-state mode		0	3.6	V
T _{amb}	ambient temperature			-40	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CCI} = 0.8 V to 3.6 V	[2]	-	5	ns/V

^[1] V_{CCO} is the supply voltage associated with the output port.

9. Static characteristics

Table 6. Typical static characteristics at T_{amb} = 25 °C

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

 V_{CCI} is the supply voltage associated with the data input port; V_{CCO} is the supply voltage associated with the output port.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{OH}	HIGH-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}; I_O = -1.5 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V}$		-	0.69	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}; I_O = 1.5 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V}$		-	0.07	-	V
l _l	input leakage current	DIR, \overline{OE} input; V _I = 0 V or 3.6 V; V _{CC(A)} = V _{CC(B)} = 0.8 V to 3.6 V		-	±0.025	±0.25	μA
l _{OZ}	OFF-state output current	A or B port; $V_O = 0$ V or V_{CCO} ; $V_{CC(A)} = V_{CC(B)} = 3.6$ V	[1]	-	±0.5	±2.5	μA
		suspend mode A port; $V_O = 0 \text{ V or } V_{CCO}$; $V_{CC(A)} = 3.6 \text{ V}$; $V_{CC(B)} = 0 \text{ V}$	[1]	-	±0.5	±2.5	μA
		suspend mode B port; $V_O = 0 \text{ V or } V_{CCO}$; $V_{CC(A)} = 0 \text{ V}$; $V_{CC(B)} = 3.6 \text{ V}$	[1]	-	±0.5	±2.5	μA
l _{OFF}	power-off leakage current	A port; V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC(A)} = 0$ V; $V_{CC(B)} = 0.8$ V to 3.6 V		-	±0.1	±1	μA
		B port; V_1 or V_0 = 0 V to 3.6 V; $V_{CC(B)}$ = 0 V; $V_{CC(A)}$ = 0.8 V to 3.6 V		-	±0.1	±1	μA
Cı	input capacitance	DIR, \overline{OE} input; V _I = 0 V or 3.3 V; V _{CC(A)} = V _{CC(B)} = 3.3 V		-	1.5	-	pF
C _{I/O}	input/output capacitance	A and B port; $V_O = 3.3 \text{ V or } 0 \text{ V};$ $V_{CC(A)} = V_{CC(B)} = 3.3 \text{ V}$		-	4.3	-	pF

^[1] For I/O ports, the parameter I_{OZ} includes the input leakage current.

V_{CCI} is the supply voltage associated with the input port.

8-bit dual supply translating transceiver with configurable voltage translation; 3-state

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

 V_{CCI} is the supply voltage associated with the data input port; V_{CCO} is the supply voltage associated with the output port.

Symbol	Parameter	Conditions	-40 °C t	o +85 °C	-40 °C to	+125 °C	Unit
			Min	Max	Min	Max	
V _{IH}	HIGH-level input	data input					
	voltage	V _{CCI} = 0.8 V	0.70V _{CCI}	-	0.70V _{CCI}	-	V
		V _{CCI} = 1.1 V to 1.95 V	0.65V _{CCI}	-	0.65V _{CCI}	-	V
		V _{CCI} = 2.3 V to 2.7 V	1.6	-	1.6	-	V
		V _{CCI} = 3.0 V to 3.6 V	2	-	2	-	V
		DIR, OE input					
		V _{CC(A)} = 0.8 V	0.70V _{CC(A)}	-	0.70V _{CC(A)}	-	V
		V _{CC(A)} = 1.1 V to 1.95 V	0.65V _{CC(A)}	-	0.65V _{CC(A)}	-	V
		V _{CC(A)} = 2.3 V to 2.7 V	1.6	-	1.6	-	V
		V _{CC(A)} = 3.0 V to 3.6 V	2	-	2	-	V
V _{IL}	LOW-level input	data input					
	voltage	V _{CCI} = 0.8 V	-	0.30V _{CCI}	-	0.30V _{CCI}	V
		V _{CCI} = 1.1 V to 1.95 V	-	0.35V _{CCI}	-	0.35V _{CCI}	V
		V _{CCI} = 2.3 V to 2.7 V	-	0.7	-	0.7	V
		V _{CCI} = 3.0 V to 3.6 V	-	0.8	-	0.8	V
		DIR, OE input					
		V _{CC(A)} = 0.8 V	-	0.30V _{CC(A)}	-	0.30V _{CC(A)}	V
		V _{CC(A)} = 1.1 V to 1.95 V	-	0.35V _{CC(A)}	-	0.35V _{CC(A)}	
		V _{CC(A)} = 2.3 V to 2.7 V	-	0.7	-	0.7	V
		V _{CC(A)} = 3.0 V to 3.6 V	-	0.8	-	0.8	V
V _{OH}	HIGH-level output	$V_I = V_{IH}$ or V_{IL}					
	voltage	I_O = -100 µA; $V_{CC(A)}$ = $V_{CC(B)}$ = 0.8 V to 3.6 V	V _{CCO} - 0.1	-	V _{CCO} - 0.1	-	V
		I_{O} = -3 mA; $V_{CC(A)}$ = $V_{CC(B)}$ = 1.1 V	0.85	-	0.85	-	V
		I_{O} = -6 mA; $V_{CC(A)}$ = $V_{CC(B)}$ = 1.4 V	1.05	-	1.05	-	V
		I_{O} = -8 mA; $V_{CC(A)}$ = $V_{CC(B)}$ = 1.65 V	1.2	-	1.2	-	V
		I_{O} = -9 mA; $V_{CC(A)}$ = $V_{CC(B)}$ = 2.3 V	1.75	-	1.75	-	V
		$I_O = -12 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 3.0 \text{ V}$	2.3	-	2.3	-	V

8-bit dual supply translating transceiver with configurable voltage translation; 3-state

Symbol	Parameter	Conditions		-40 °C t	o +85 °C	-40 °C to	+125 °C	Unit
				Min	Max	Min	Max	
V _{OL}	LOW-level output	V _I = V _{IH} or V _{IL}						
	voltage	$I_O = 100 \mu A;$ $V_{CC(A)} = V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$		-	0.1	-	0.1	V
		I _O = 3 mA; V _{CC(A)} = V _{CC(B)} = 1.1 V		-	0.25	-	0.25	V
		$I_{O} = 6 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 1.4 \text{ V}$		-	0.35	-	0.35	V
		I _O = 8 mA; V _{CC(A)} = V _{CC(B)} = 1.65 V		-	0.45	-	0.45	V
		$I_O = 9 \text{ mA};$ $V_{CC(A)} = V_{CC(B)} = 2.3 \text{ V}$		-	0.55	-	0.55	V
		I_{O} = 12 mA; $V_{CC(A)} = V_{CC(B)} = 3.0 \text{ V}$		-	0.7	-	0.7	V
l _l	input leakage current	DIR, \overline{OE} input; V _I = 0 V or 3.6 V; V _{CC(A)} = V _{CC(B)} = 0.8 V to 3.6 V		-	±1	-	±5	μA
l _{OZ}	OFF-state output current	A or B port; $V_O = 0 \text{ V or } V_{CCO}$; $V_{CC(A)} = V_{CC(B)} = 3.6 \text{ V}$	[1]	-	±5	-	±30	μA
		suspend mode A port; $V_O = 0 \text{ V or } V_{CCO}; V_{CC(A)} = 3.6 \text{ V};$ $V_{CC(B)} = 0 \text{ V}$	[1]	-	±5	-	±30	μA
		suspend mode B port; $V_O = 0 \text{ V or } V_{CCO}; V_{CC(A)} = 0 \text{ V};$ $V_{CC(B)} = 3.6 \text{ V}$	[1]	-	±5	-	±30	μA
U	power-off leakage current	A port; V_1 or V_0 = 0 V to 3.6 V; $V_{CC(A)}$ = 0 V; $V_{CC(B)}$ = 0.8 V to 3.6 V		-	±5	-	±30	μΑ
		B port; V_1 or V_0 = 0 V to 3.6 V; $V_{CC(B)}$ = 0 V; $V_{CC(A)}$ = 0.8 V to 3.6 V		-	±5	-	±30	μA

8-bit dual supply translating transceiver with configurable voltage translation; 3-state

Symbol	Parameter	Conditions	-40 °C t	o +85 °C	-40 °C to	+125 °C	Unit
			Min	Max	Min	Max	
I _{CC}	supply current	A port; $V_I = 0 \text{ V or } V_{CCI}$; $I_O = 0 \text{ A}$					
		$V_{CC(A)} = 0.8 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	-	10	-	55	μA
		$V_{CC(A)} = 1.1 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	8	-	50	μA
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(B)} = 0 \text{ V}$	-	8	-	50	μΑ
		$V_{CC(A)} = 0 \text{ V}; V_{CC(B)} = 3.6 \text{ V}$	-2	-	-12	-	μA
		B port; $V_I = 0 \text{ V or } V_{CCI}$; $I_O = 0 \text{ A}$					
		$V_{CC(A)} = 0.8 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 0.8 \text{ V to } 3.6 \text{ V}$	-	10	-	55	μA
		$V_{CC(A)} = 1.1 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 1.1 \text{ V to } 3.6 \text{ V}$	-	8	-	50	μA
		V _{CC(A)} = 3.6 V; V _{CC(B)} = 0 V	-2	-	-12	-	μA
		$V_{CC(A)} = 0 \text{ V}; V_{CC(B)} = 3.6 \text{ V}$	-	8	-	50	μΑ
		A plus B port ($I_{CC(A)} + I_{CC(B)}$); $I_O = 0$ A; $V_I = 0$ V or V_{CCI} ; $V_{CC(A)} = 0.8$ V to 3.6 V; $V_{CC(B)} = 0.8$ V to 3.6 V	-	20	-	70	μА
		A plus B port ($I_{CC(A)} + I_{CC(B)}$); $I_O = 0$ A; $V_I = 0$ V or V_{CCI} ; $V_{CC(A)} = 1.1$ V to 3.6 V; $V_{CC(B)} = 1.1$ V to 3.6 V	-	16	-	65	μА

^[1] For I/O ports, the parameter I_{OZ} includes the input leakage current.

Table 8. Typical total supply current $(I_{CC(A)} + I_{CC(B)})$

V _{CC(A)}		,,,,,	., 55(2),	V _{CC(B)}				Unit
	0 V	0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
0 V	0	0.1	0.1	0.1	0.1	0.1	0.1	μΑ
0.8 V	0.1	0.1	0.1	0.1	0.1	0.3	1.6	μA
1.2 V	0.1	0.1	0.1	0.1	0.1	0.1	0.8	μΑ
1.5 V	0.1	0.1	0.1	0.1	0.1	0.1	0.4	μΑ
1.8 V	0.1	0.1	0.1	0.1	0.1	0.1	0.2	μΑ
2.5 V	0.1	0.3	0.1	0.1	0.1	0.1	0.1	μΑ
3.3 V	0.1	1.6	0.8	0.4	0.2	0.1	0.1	μΑ

8-bit dual supply translating transceiver with configurable voltage translation; 3-state

10. Dynamic characteristics

Table 9. Typical dynamic characteristics at $V_{CC(A)}$ = 0.8 V and T_{amb} = 25 °C

Voltages are referenced to GND (ground = 0 V); for test circuit see Fig. 7; for wave forms see Fig. 5 and Fig. 6. t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} .

Symbol Parameter Conditions V _{CC(B)}							Unit		
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
t _{pd} p	propagation delay	An to Bn	14.4	7.0	6.2	6.0	5.9	6.0	ns
		Bn to An	14.4	12.4	12.1	11.9	11.8	11.8	ns
t _{dis}	disable time	OE to An	16.2	16.2	16.2	16.2	16.2	16.2	ns
		OE to Bn	17.6	10.0	9.0	9.1	8.7	9.3	ns
t _{en}	enable time	OE to An	21.9	21.9	21.9	21.9	21.9	21.9	ns
		OE to Bn	22.2	11.1	9.8	9.4	9.4	9.6	ns

Table 10. Typical dynamic characteristics at $V_{CC(B)}$ = 0.8 V and T_{amb} = 25 °C

Voltages are referenced to GND (ground = 0 V); for test circuit see Fig. 7; for wave forms see Fig. 5 and Fig. 6. t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} .

Symbol	Parameter	Conditions	V _{CC(A)}						
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V]
t _{pd}	propagation delay	An to Bn	14.4	12.4	12.1	11.9	11.8	11.8	ns
		Bn to An	14.4	7.0	6.2	6.0	5.9	6.0	ns
t _{dis}	disable time	OE to An	16.2	5.9	4.4	4.2	3.1	3.5	ns
		OE to Bn	17.6	14.2	13.7	13.6	13.3	13.1	ns
t _{en}	enable time	OE to An	21.9	6.4	4.4	3.5	2.6	2.3	ns
		OE to Bn	22.2	17.7	17.2	17.0	16.8	16.7	ns

8-bit dual supply translating transceiver with configurable voltage translation; 3-state

Table 11. Typical power dissipation capacitance at $V_{CC(A)} = V_{CC(B)}$ and $T_{amb} = 25 \, ^{\circ}C$

Voltages are referenced to GND (ground = 0 V). [1] [2]

Symbol	Parameter	Conditions			V _{CC(A)} :	= V _{CC(B)}			Unit
			0.8 V	1.2 V	1.5 V	1.8 V	2.5 V	3.3 V	
C _{PD}	power dissipation capacitance	A port: (direction An to Bn); output enabled	0.2	0.2	0.2	0.3	0.4	0.5	pF
		A port: (direction An to Bn); output disabled	0.2	0.2	0.2	0.3	0.4	0.5	pF
		A port: (direction Bn to An); output enabled	9	9	10	10	11	13	pF
		A port: (direction Bn to An); output disabled	0.6	0.6	0.6	0.7	0.7	0.8	pF
		B port: (direction An to Bn); output enabled	9	9	10	10	11	13	pF
		B port: (direction An to Bn); output disabled	0.6	0.6	0.6	0.7	0.7	0.8	pF
		B port: (direction Bn to An); output enabled	0.2	0.2	0.2	0.3	0.4	0.5	pF
		B port: (direction Bn to An); output disabled	0.2	0.2	0.2	0.3	0.4	0.5	pF

[1] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:

 f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o) = \text{sum of the outputs.}$ [2] $f_i = 10 \text{ MHz}$; $V_i = \text{GND to } V_{CC}$; $t_r = t_f = 1 \text{ ns}$; $C_L = 0 \text{ pF}$; $R_L = \infty \Omega$.

10 / 23

8-bit dual supply translating transceiver with configurable voltage translation; 3-state

Table 12. Dynamic characteristics for temperature range -40 °C to +85 °C

Voltages are referenced to GND (ground = 0 V); for test circuit see Fig. 7; for wave forms see Fig. 5 and Fig. 6. t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} .

Symbol	Parameter	Conditions					V _C	C(B)					Unit
			1.2 V	± 0.1 V	1.5 V	± 0.1 V	1.8 V ±	0.15 V	2.5 V	± 0.2 V	3.3 V	± 0.3 V	1
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	1
V _{CC(A)} =	1.1 V to 1.3 V						'	'					'
t _{pd}	propagation	An to Bn	0.5	9.0	0.5	6.7	0.5	5.8	0.5	4.9	0.5	4.8	ns
	delay	Bn to An	0.5	9.0	0.5	8.5	0.5	8.3	0.5	8.0	0.5	7.8	ns
t _{dis}	disable time	OE to An	0.5	11.8	0.5	11.8	0.5	11.8	0.5	11.8	0.5	11.8	ns
		OE to Bn	0.5	12.3	0.5	9.5	0.5	9.4	0.5	8.0	0.5	8.9	ns
t _{en}	enable time	OE to An	1.1	14.4	1.1	14.4	1.1	14.4	1.1	14.4	1.1	14.4	ns
		OE to Bn	1.1	14.2	1.1	10.4	1.1	9.0	1.0	7.7	1.0	7.3	ns
V _{CC(A)} =	1.4 V to 1.6 V												
t _{pd}	propagation	An to Bn	0.5	8.5	0.5	5.6	0.5	4.7	0.5	4.4	0.5	4.1	ns
	delay	Bn to An	0.5	6.7	0.5	5.6	0.5	5.3	0.5	5.2	0.5	5.0	ns
t _{dis}	disable time	OE to An	0.5	8.6	0.5	8.6	0.5	8.6	0.5	8.6	0.5	8.6	ns
		OE to Bn	0.5	11.2	0.5	8.4	0.5	7.6	0.5	7.2	0.5	7.8	ns
t _{en}	enable time	OE to An	1.1	8.7	1.1	8.7	1.1	8.7	1.1	8.7	1.1	8.7	ns
		OE to Bn	1.1	12.8	1.1	8.1	1.1	7.1	1.0	5.6	1.0	5.2	ns
V _{CC(A)} =	1.65 V to 1.95	5 V				1							
t _{pd}	propagation	An to Bn	0.5	8.3	0.5	5.3	0.5	4.5	0.5	3.8	0.5	3.5	ns
	delay	Bn to An	0.5	5.8	0.5	4.7	0.5	4.5	0.5	4.3	0.5	4.1	ns
t _{dis}	disable time	OE to An	0.5	7.1	0.5	7.1	0.5	7.1	0.5	7.1	0.5	7.1	ns
		OE to Bn	0.5	10.9	0.5	7.8	0.5	6.9	0.5	6.0	0.5	5.8	ns
t _{en}	enable time	OE to An	1.0	6.8	1.0	6.8	1.0	6.8	1.0	6.8	1.0	6.8	ns
		OE to Bn	1.1	12.4	1.1	8.2	1.0	6.7	0.5	5.1	0.5	4.5	ns
V _{CC(A)} =	2.3 V to 2.7 V												
t _{pd}	propagation	An to Bn	0.5	8.0	0.5	5.2	0.5	4.3	0.5	3.3	0.5	2.9	ns
	delay	Bn to An	0.5	4.9	0.5	4.4	0.5	3.8	0.5	3.3	0.5	3.1	ns
t _{dis}	disable time	OE to An	0.5	5.1	0.5	5.1	0.5	5.1	0.5	5.1	0.5	5.1	ns
		OE to Bn	0.5	10.4	0.5	7.1	0.5	6.3	0.5	5.1	0.5	5.2	ns
t _{en}	enable time	OE to An	0.5	4.8	0.5	4.8	0.5	4.8	0.5	4.8	0.5	4.8	ns
		OE to Bn	1.1	11.9	1.1	7.9	0.5	6.4	0.5	4.6	0.5	4.0	ns
V _{CC(A)} =	3.0 V to 3.6 V	,											
t _{pd}	propagation	An to Bn	0.5	7.8	0.5	5.0	0.5	4.1	0.5	3.1	0.5	2.7	ns
	delay	Bn to An	0.5	4.8	0.5	4.1	0.5	3.5	0.5	2.9	0.5	2.7	ns
t _{dis}	disable time	OE to An	0.5	4.9	0.5	4.9	0.5	4.9	0.5	4.9	0.5	4.9	ns
		OE to Bn	0.5	10.1	0.5	6.9	0.5	6.0	0.5	4.8	0.5	5.0	ns
t _{en}	enable time	OE to An	0.5	4.0	0.5	4.0	0.5	4.0	0.5	4.0	0.5	4.0	ns
		OE to Bn	1.1	11.7	1.1	7.8	0.5	6.2	0.5	4.5	0.5	3.9	ns

8-bit dual supply translating transceiver with configurable voltage translation; 3-state

Table 13. Dynamic characteristics for temperature range -40 °C to +125 °C

Voltages are referenced to GND (ground = 0 V); for test circuit see Fig. 7; for wave forms see Fig. 5 and Fig. 6 t_{pd} is the same as t_{PLH} and t_{PHL} ; t_{dis} is the same as t_{PLZ} and t_{PHZ} ; t_{en} is the same as t_{PZL} and t_{PZH} .

Symbol	Parameter	Conditions					V _C	C(B)					Unit
			1.2 V	± 0.1 V	1.5 V	± 0.1 V	1.8 V ±	0.15 V	2.5 V	± 0.2 V	3.3 V	± 0.3 V	
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
V _{CC(A)} =	1.1 V to 1.3 V												
t _{pd}	propagation	An to Bn	0.5	9.9	0.5	7.4	0.5	6.4	0.5	5.4	0.5	5.3	ns
	delay	Bn to An	0.5	9.9	0.5	9.4	0.5	9.2	0.5	8.8	0.5	8.6	ns
t _{dis}	disable time	OE to An	0.5	13.0	0.5	13.0	0.5	13.0	0.5	13.0	0.5	13.0	ns
		OE to Bn	0.5	13.6	0.5	10.5	0.5	10.4	0.5	8.8	0.5	9.8	ns
t _{en}	enable time	OE to An	1.1	15.9	1.1	15.9	1.1	15.9	1.1	15.9	1.1	15.9	ns
		OE to Bn	1.1	15.7	1.1	11.5	1.1	9.9	1.0	8.5	1.0	8.1	ns
V _{CC(A)} =	1.4 V to 1.6 V												
t _{pd}	propagation	An to Bn	0.5	9.4	0.5	6.2	0.5	5.2	0.5	4.9	0.5	4.6	ns
	delay	Bn to An	0.5	7.4	0.5	6.2	0.5	5.9	0.5	5.8	0.5	5.5	ns
t _{dis}	disable time	OE to An	0.5	9.5	0.5	9.5	0.5	9.5	0.5	9.5	0.5	9.5	ns
		OE to Bn	0.5	12.4	0.5	9.3	0.5	8.4	0.5	8.0	0.5	8.6	ns
t _{en}	enable time	OE to An	1.1	9.6	1.1	9.6	1.1	9.6	1.1	9.6	1.1	9.6	ns
		OE to Bn	1.1	14.1	1.1	9.0	1.1	7.9	1.0	6.2	1.0	5.8	ns
V _{CC(A)} =	1.65 V to 1.95	V											
t _{pd}	propagation	An to Bn	0.5	9.2	0.5	5.9	0.5	5.0	0.5	4.2	0.5	3.9	ns
	delay	Bn to An	0.5	6.4	0.5	5.2	0.5	5.0	0.5	4.8	0.5	4.6	ns
t _{dis}	disable time	OE to An	0.5	7.9	0.5	7.9	0.5	7.9	0.5	7.9	0.5	7.9	ns
		OE to Bn	0.5	12.0	0.5	8.6	0.5	7.6	0.5	6.6	0.5	6.4	ns
t _{en}	enable time	OE to An	1.0	7.5	1.0	7.5	1.0	7.5	1.0	7.5	1.0	7.5	ns
		OE to Bn	1.1	13.7	1.1	9.1	1.0	7.4	0.5	5.7	0.5	5.0	ns
V _{CC(A)} =	2.3 V to 2.7 V												
t _{pd}	propagation	An to Bn	0.5	8.8	0.5	5.8	0.5	4.8	0.5	3.7	0.5	3.2	ns
	delay	Bn to An	0.5	5.4	0.5	4.9	0.5	4.2	0.5	3.7	0.5	3.5	ns
t _{dis}	disable time	OE to An	0.5	5.7	0.5	5.7	0.5	5.7	0.5	5.7	0.5	5.7	ns
		OE to Bn	0.5	11.5	0.5	7.9	0.5	7.0	0.5	5.7	0.5	5.8	ns
t _{en}	enable time	OE to An	0.5	5.3	0.5	5.3	0.5	5.3	0.5	5.3	0.5	5.3	ns
		OE to Bn	1.1	13.1	1.1	8.7	0.5	7.1	0.5	5.1	0.5	4.4	ns
V _{CC(A)} =	3.0 V to 3.6 V												
t _{pd}	propagation	An to Bn	0.5	8.6	0.5	5.5	0.5	4.6	0.5	3.5	0.5	3.0	ns
	delay	Bn to An	0.5	5.3	0.5	4.6	0.5	3.9	0.5	3.2	0.5	3.0	ns
t _{dis}	disable time	OE to An	0.5	5.4	0.5	5.4	0.5	5.4	0.5	5.4	0.5	5.4	ns
		OE to Bn	0.5	11.2	0.5	7.6	0.5	6.6	0.5	5.3	0.5	5.5	ns
t _{en}	enable time	OE to An	0.5	4.4	0.5	4.4	0.5	4.4	0.5	4.4	0.5	4.4	ns
en		OE to Bn	1.1	12.9	1.1	8.6	0.5	6.9	0.5	5.0	0.5	4.3	ns

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10.1. Waveforms and test circuit

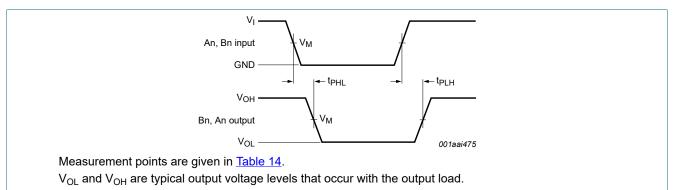


Fig. 5. The data input (An, Bn) to output (Bn, An) propagation delay times

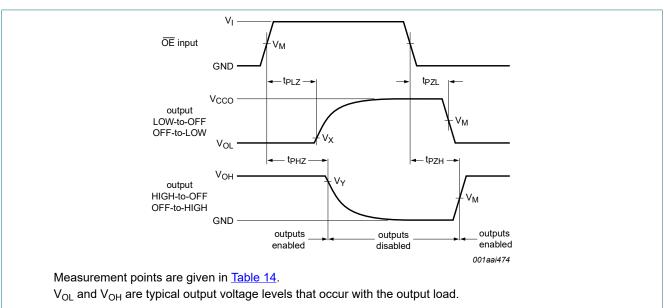


Fig. 6. Enable and disable times

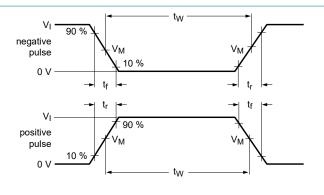
Table 14. Measurement points

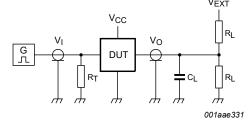
	water the modern entering points										
Supply voltage	Input [1]	Output [2]	Output [2]								
V _{CC(A)} , V _{CC(B)}	V _M	V _M	V _X	V _Y							
0.8 V to 1.6 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.1 V	V _{OH} - 0.1 V							
1.65 V to 2.7 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.15 V	V _{OH} - 0.15 V							
3.0 V to 3.6 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.3 V	V _{OH} - 0.3 V							

^[1] V_{CCI} is the supply voltage associated with the data input port.

^[2] V_{CCO} is the supply voltage associated with the output port.

8-bit dual supply translating transceiver with configurable voltage translation; 3-state





Test data is given in Table 15.

 R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance.

V_{EXT} = External voltage for measuring switching times.

Fig. 7. Test circuit for measuring switching times

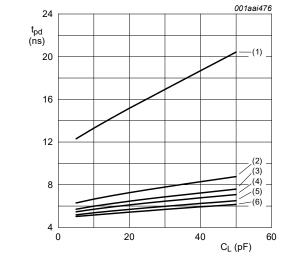
Table 15. Test data

Supply voltage	ly voltage Input		Load		V _{EXT}			
$V_{CC(A)}, V_{CC(B)}$	V _I [1]	Δt/ΔV [2]	CL	R_L	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ} [3]	
0.8 V to 1.6 V	V _{CCI}	≤1.0 ns/V	15 pF	2 kΩ	open	GND	2V _{CCO}	
1.65 V to 2.7 V	V _{CCI}	≤ 1.0 ns/V	15 pF	2 kΩ	open	GND	2V _{CCO}	
3.0 V to 3.6 V	V _{CCI}	≤ 1.0 ns/V	15 pF	2 kΩ	open	GND	2V _{CCO}	

- [1] V_{CCI} is the supply voltage associated with the data input port.
- [2] dV/dt ≥ 1.0 V/ns
- [3] V_{CCO} is the supply voltage associated with the output port.

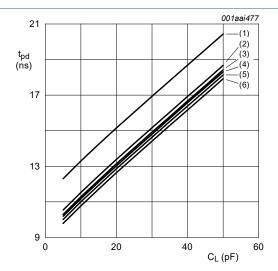
8-bit dual supply translating transceiver with configurable voltage translation; 3-state

10.2. Typical propagation delay characteristics



- a. Propagation delay (An to Bn); $V_{CC(A)} = 0.8 \text{ V}$
 - (1) $V_{CC(B)} = 0.8 \text{ V}.$
 - (2) $V_{CC(B)} = 1.2 \text{ V}.$ (3) $V_{CC(B)} = 1.5 \text{ V}.$

 - (4) $V_{CC(B)} = 1.8 \text{ V}.$
 - (5) $V_{CC(B)} = 2.5 \text{ V}.$ (6) $V_{CC(B)} = 3.3 \text{ V}.$

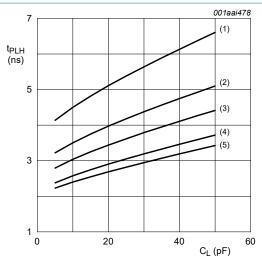


- b. Propagation delay (An to Bn); $V_{CC(B)} = 0.8 \text{ V}$
 - (1) $V_{CC(A)} = 0.8 \text{ V}.$
 - (2) $V_{CC(A)} = 1.2 \text{ V}.$ (3) $V_{CC(A)} = 1.5 \text{ V}.$

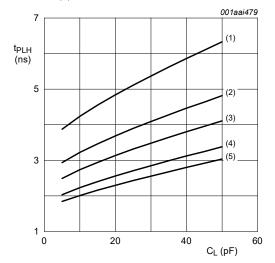
 - (4) $V_{CC(A)} = 1.8 \text{ V}.$ (5) $V_{CC(A)} = 2.5 \text{ V}.$
 - (6) $V_{CC(A)} = 3.3 \text{ V}.$

Typical propagation delay versus load capacitance; T_{amb} = 25 °C Fig. 8.

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a. LOW to HIGH propagation delay (An to Bn); $V_{CC(A)} = 1.2 \text{ V}$

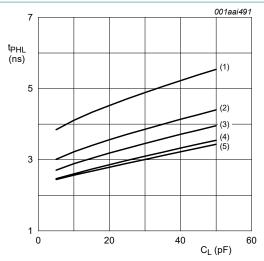


c. LOW to HIGH propagation delay (An to Bn); $V_{CC(A)} = 1.5 \text{ V}$

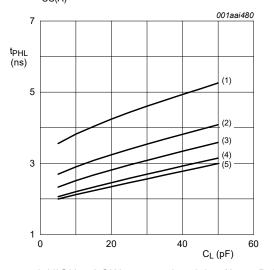
- (1) $V_{CC(B)} = 1.2 \text{ V}.$
- (2) $V_{CC(B)} = 1.5 \text{ V.}$ (3) $V_{CC(B)} = 1.8 \text{ V.}$ (4) $V_{CC(B)} = 2.5 \text{ V.}$

- (5) $V_{CC(B)} = 3.3 \text{ V}.$



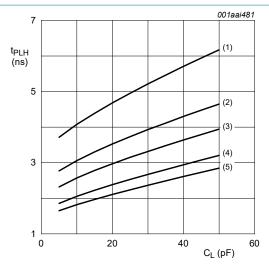


b. HIGH to LOW propagation delay (An to Bn); $V_{CC(A)} = 1.2 \text{ V}$

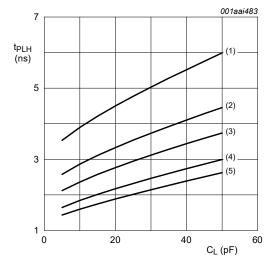


d. HIGH to LOW propagation delay (An to Bn); $V_{CC(A)} = 1.5 \text{ V}$

8-bit dual supply translating transceiver with configurable voltage translation; 3-state



a. LOW to HIGH propagation delay (An to Bn); $V_{CC(A)} = 1.8 \text{ V}$

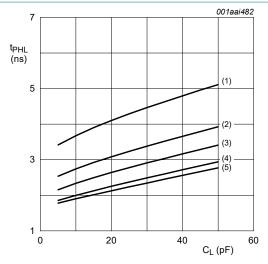


c. LOW to HIGH propagation delay (An to Bn); $V_{CC(A)} = 2.5 \text{ V}$

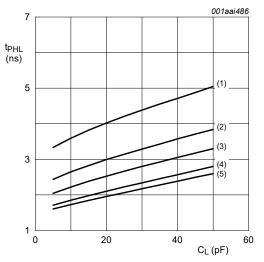
- (1) $V_{CC(B)} = 1.2 \text{ V}.$
- (2) $V_{CC(B)} = 1.5 \text{ V}.$ (3) $V_{CC(B)} = 1.8 \text{ V}.$ (4) $V_{CC(B)} = 2.5 \text{ V}.$

- (5) $V_{CC(B)} = 3.3 \text{ V}.$

Fig. 10. Typical propagation delay versus load capacitance; T_{amb} = 25 °C

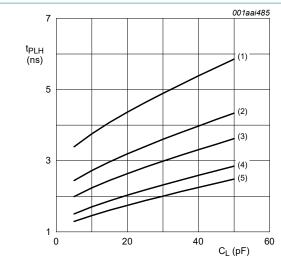


b. HIGH to LOW propagation delay (An to Bn); $V_{CC(A)} = 1.8 \text{ V}$



d. HIGH to LOW propagation delay (An to Bn); $V_{CC(A)} = 2.5 \text{ V}$

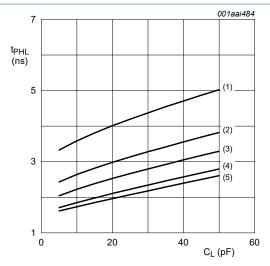
8-bit dual supply translating transceiver with configurable voltage translation; 3-state



a. LOW to HIGH propagation delay (An to Bn); $V_{CC(A)} = 3.3 \text{ V}$

- (1) $V_{CC(B)} = 1.2 \text{ V}.$

 - (2) $V_{CC(B)} = 1.5 \text{ V}.$ (3) $V_{CC(B)} = 1.8 \text{ V}.$
 - (4) $V_{CC(B)} = 2.5 \text{ V}.$ (5) $V_{CC(B)} = 3.3 \text{ V}.$



b. HIGH to LOW propagation delay (An to Bn); $V_{CC(A)} = 3.3 \text{ V}$

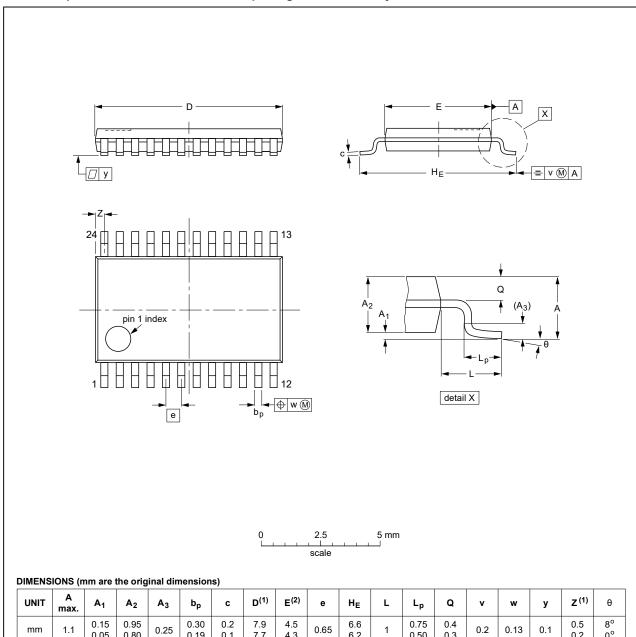
Fig. 11. Typical propagation delay versus load capacitance; T_{amb} = 25 °C

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11. Package outline

TSSOP24: plastic thin shrink small outline package; 24 leads; body width 4.4 mm

SOT355-1



UNIT	A max.	A ₁	A ₂	A ₃	b _p	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	7.9 7.7	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.5 0.2	8° 0°

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT355-1		MO-153				99-12-27 03-02-19	

Fig. 12. Package outline SOT355-1 (TSSOP24)

8-bit dual supply translating transceiver with configurable voltage translation; 3-state

DHVQFN24: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 24 terminals; body 3.5 x 5.5 x 0.85 mm

SOT815-1

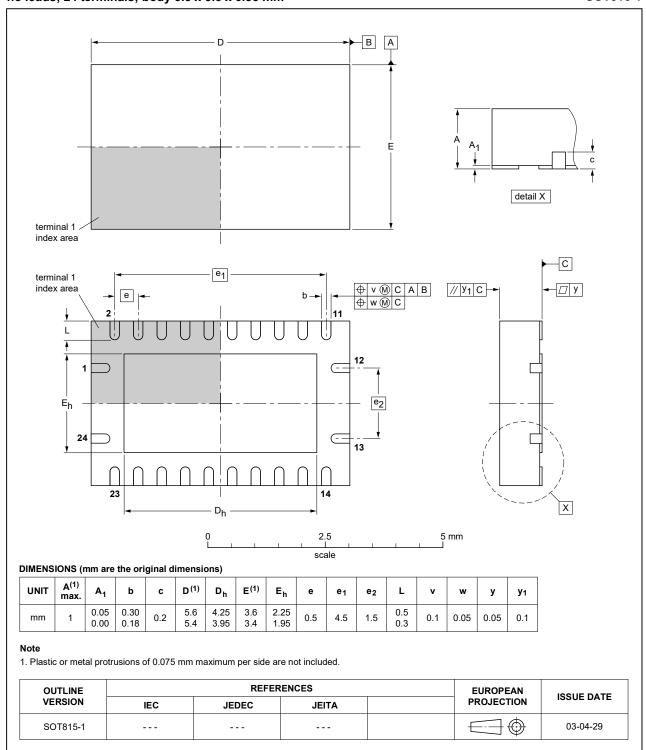


Fig. 13. Package outline SOT815-1 (DHVQFN24)

8-bit dual supply translating transceiver with configurable voltage translation; 3-state

12. Abbreviations

Table 16. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model

13. Revision history

Table 17. Revision history

- Revision histo				
Document ID	Release date	Data sheet status	Change notice	Supersedes
74AVC8T245 v.6	20200331	Product data sheet	-	74AVC8T245 v.5
Modifications:	guidelines • Legal texts	t of this data sheet has been of Nexperia. Is have been adapted to the erating values for P _{tot} total	new company nar	me where appropriate.
74AVC8T245 v.5	20121227	Product data sheet	-	74AVC8T245 v.4
Modifications:	• <u>Table 4</u> : co	onditions I _{CC} and I _{GND} char	nged (errata).	
74AVC8T245 v.4	20111208	Product data sheet	-	74AVC8T245 v.3
Modifications:	Legal page	es updated.	,	
74AVC8T245 v.3	20110928	Product data sheet	-	74AVC8T245 v.2
74AVC8T245 v.2	20090428	Product data sheet	-	74AVC8T245 v.1
74AVC8T245 v.1	20080711	Product data sheet	-	-

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14. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at https://www.nexperia.com.

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8-bit dual supply translating transceiver with configurable voltage translation; 3-state

Contents

1. General description	1
2. Features and benefits	1
3. Ordering information	2
4. Functional diagram	2
5. Pinning information	3
5.1. Pinning	3
5.2. Pin description	3
6. Functional description	4
7. Limiting values	
8. Recommended operating conditions	5
9. Static characteristics	
10. Dynamic characteristics	9
10.1. Waveforms and test circuit	13
10.2. Typical propagation delay characteristics	15
11. Package outline	19
12. Abbreviations	21
13. Revision history	21
14. Legal information	
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